

# 30V N-Channel Enhancement Mode MOSFET

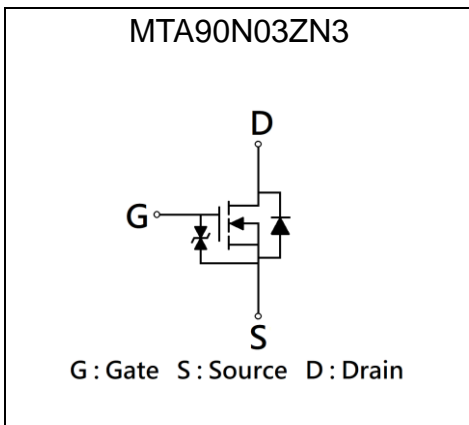
## MTA90N03ZN3

|                                      |                     |
|--------------------------------------|---------------------|
| $BV_{DSS}$                           | 30V                 |
| $I_D$                                | 3.2A                |
| $R_{DS(on)} @ V_{GS}=4.5V, I_D=2.5A$ | 130m $\Omega$ (typ) |
| $R_{DS(on)} @ V_{GS}=3V, I_D=2.5A$   | 144m $\Omega$ (typ) |

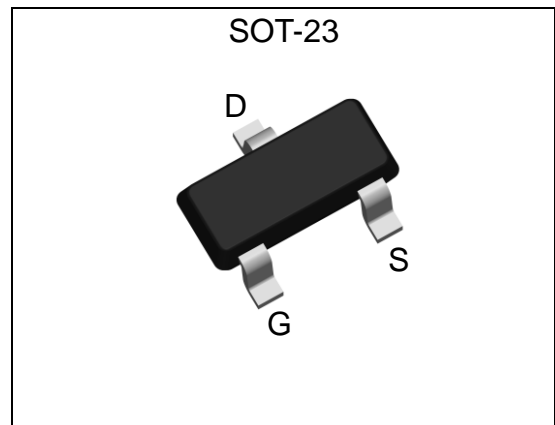
### Features

- Simple drive requirement.
- Small package outline.
- ESD protected.
- Pb-free lead plating and halogen-free package.

### Symbol



### Outline



### Absolute Maximum Ratings (Ta=25°C)

| Parameter  | Symbol         | Limits        | Unit          |
|--|----------------|---------------|---------------|
| Drain-Source Voltage   | $V_{DS}$       | 30            | V             |
| Gate-Source Voltage  | $V_{GS}$       | $\pm 12$      |               |
| Continuous Drain Current @ $T_A=25^\circ C$ , $V_{GS}=4.5V$            | $I_D$          | 3.2           | A             |
| Continuous Drain Current @ $T_A=70^\circ C$ , $V_{GS}=4.5V$            |                | 2.6           |               |
| Pulsed Drain Current (Notes 1, 2)                                      | $I_{DM}$       | 10            |               |
| Maximum Power Dissipation @ $T_A=25^\circ C$<br>Linear Derating Factor | $P_D$          | 1.38 (Note 3) | W             |
|  |                | 0.01          | W/ $^\circ C$ |
| ESD susceptibility   |                | 1000 (Note 4) | V             |
| Operating Junction and Storage Temperature                             | $T_j, T_{stg}$ | -55~+150      | $^\circ C$    |

- Note : 1. Pulse width limited by maximum junction temperature.  
 2. Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .  
 3. Surface mounted on 1 in<sup>2</sup> copper pad of FR-4 board,  $t \leq 10s$ .  
 4. Human body model, 1.5k $\Omega$  in series with 100pF.

**Thermal Performance**

| Parameter  | Symbol | Limit | Unit |
|--|--------|-------|------|
| Thermal Resistance, Junction-to-Ambient(PCB mounted) | Rth,ja | 90    | °C/W |

Note : Surface mounted on 1 in<sup>2</sup> copper pad of FR-4 board, 270°C/W when mounted on minimum copper pad.

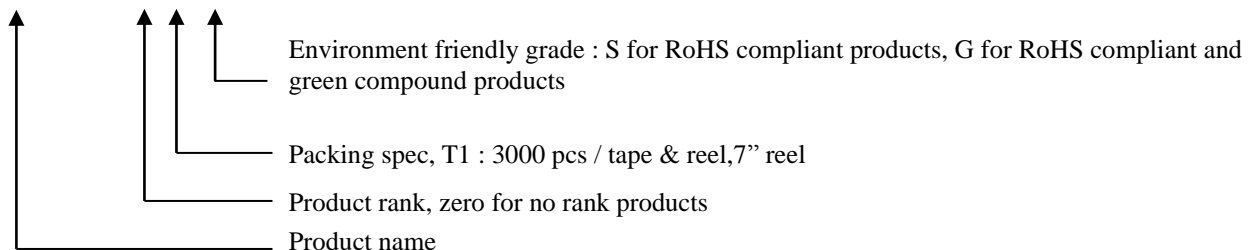
**Electrical Characteristics (T<sub>j</sub>=25°C, unless otherwise noted)**

| Symbol                    | Min. | Typ. | Max. | Unit | Test Conditions   |
|---------------------------|------|------|------|------|---|
| <b>Static</b>             |      |      |      |      |   |
| BV <sub>DSS</sub>         | 30   | -    | -    | V    | V <sub>GS</sub> =0, I <sub>D</sub> =250μA   |
| V <sub>GS(th)</sub>       | 0.5  | 0.9  | 1.5  | V    | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA                                  |
| I <sub>GSS</sub>          | -    | -    | ±10  | μA   | V <sub>GS</sub> =±12V, V <sub>DS</sub> =0   |
| I <sub>DSS</sub>          | -    | -    | 1    |      | V <sub>DS</sub> =24V, V <sub>GS</sub> =0  |
| *R <sub>DS(ON)</sub>      | -    | 130  | 160  | mΩ   | V <sub>GS</sub> =4.5V, I <sub>D</sub> =2.5A   |
|                           | -    | 145  | 180  |      | V <sub>GS</sub> =3V, I <sub>D</sub> =2.5A   |
| *G <sub>FS</sub>          | -    | 5.4  | -    | S    | V <sub>DS</sub> =3V, I <sub>D</sub> =1.6A   |
| <b>Dynamic</b>            |      |      |      |      |   |
| C <sub>iss</sub>          | -    | 309  | -    | pF   | V <sub>DS</sub> =10V, V <sub>GS</sub> =0, f=1MHz  |
| C <sub>oss</sub>          | -    | 50   | -    |      |   |
| C <sub>rss</sub>          | -    | 38   | -    |      |   |
| t <sub>d(ON)</sub>        | -    | 15   | -    | ns   | V <sub>DS</sub> =15V, I <sub>D</sub> =500mA, V <sub>GS</sub> =2.5V,<br>R <sub>G</sub> =6Ω |
| t <sub>r</sub>            | -    | 35   | -    |      |   |
| t <sub>d(OFF)</sub>       | -    | 51   | -    |      |   |
| t <sub>f</sub>            | -    | 27   | -    |      |   |
| Q <sub>g</sub>            | -    | 8    | -    | nC   | V <sub>DS</sub> =15V, I <sub>D</sub> =3.2A, V <sub>GS</sub> =4.5V                         |
| Q <sub>gs</sub>           | -    | 0.8  | -    |      |   |
| Q <sub>gd</sub>           | -    | 2.8  | -    |      |   |
| <b>Source-Drain Diode</b> |      |      |      |      |   |
| *V <sub>SD</sub>          | -    | 0.8  | 1.2  | V    | V <sub>GS</sub> =0V, I <sub>S</sub> =1A   |

\*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

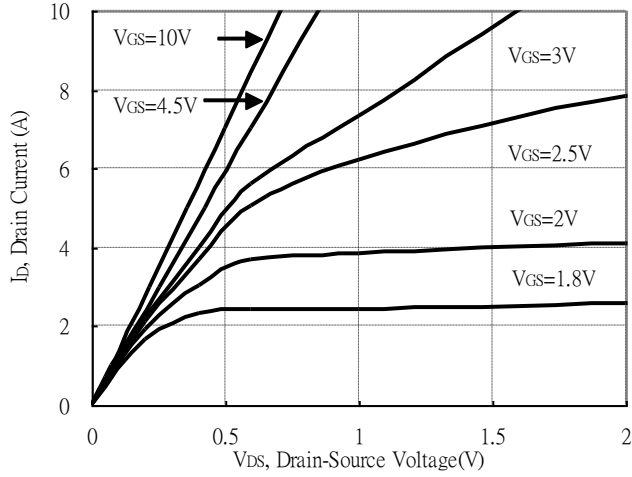
**Ordering Information**

| Device             | Package   | Shipping               |
|--------------------|---|------------------------|
| MTA90N03ZN3-0-T1-G | SOT-23<br>(Pb-free lead plating and halogen-free package) | 3000 pcs / tape & reel |

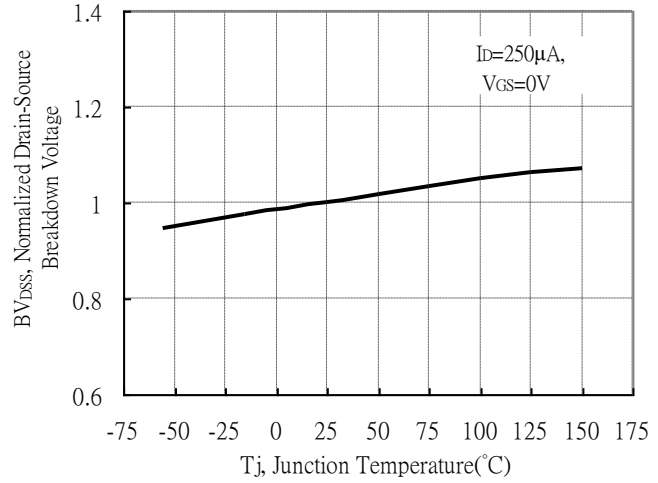


## Typical Characteristics

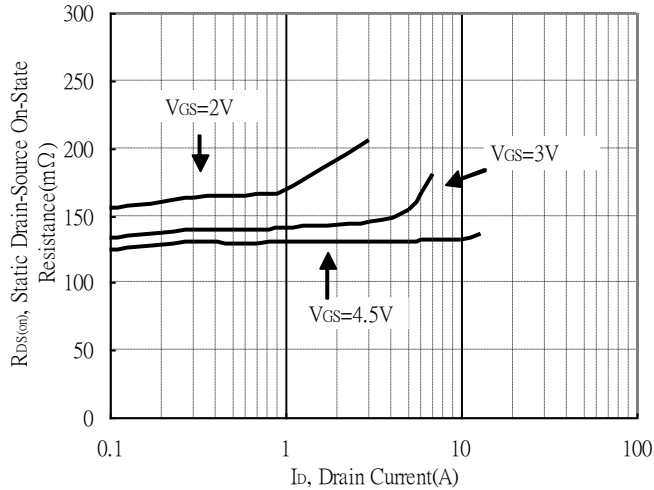
Typical Output Characteristics



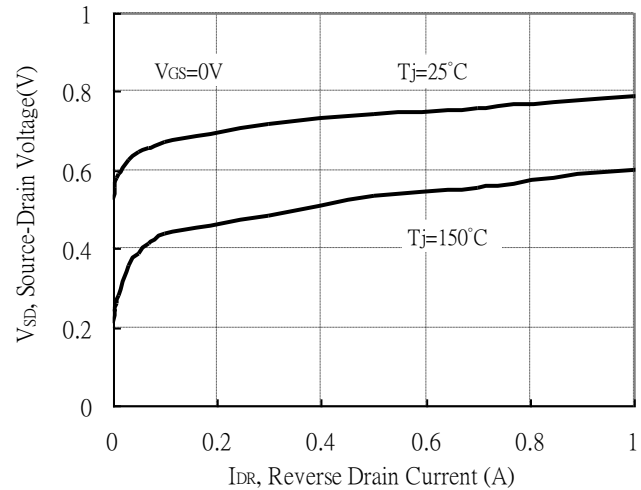
Brekdown Voltage vs Ambient Temperature



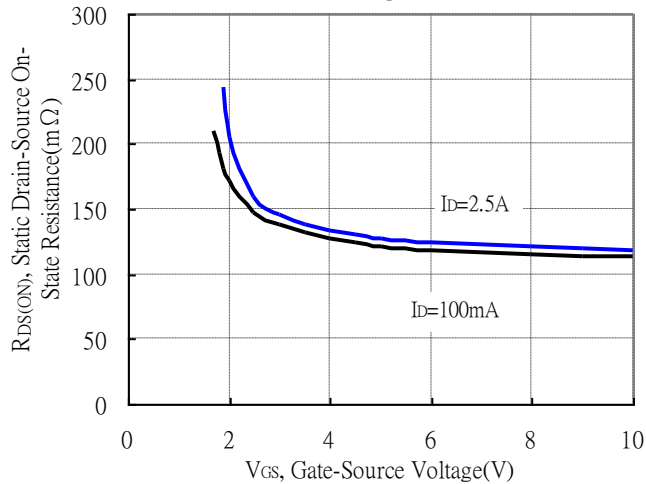
Static Drain-Source On-State resistance vs Drain Current



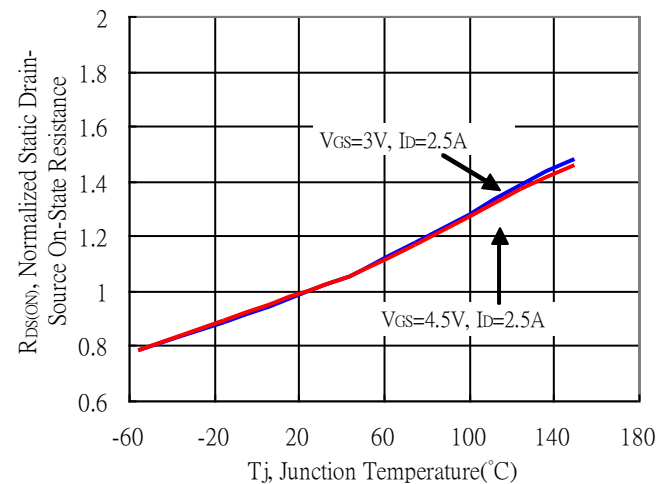
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

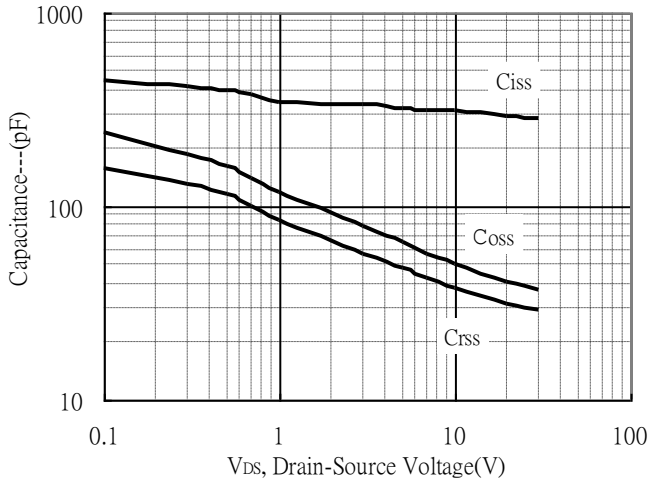


Drain-Source On-State Resistance vs Junction Temperature

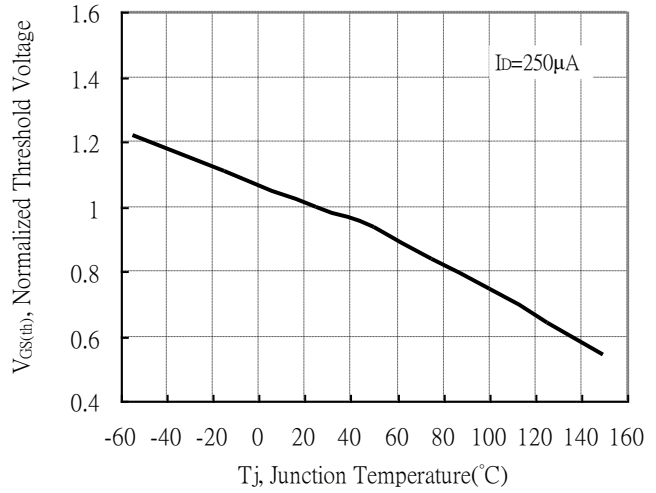


**Typical Characteristics(Cont.)**

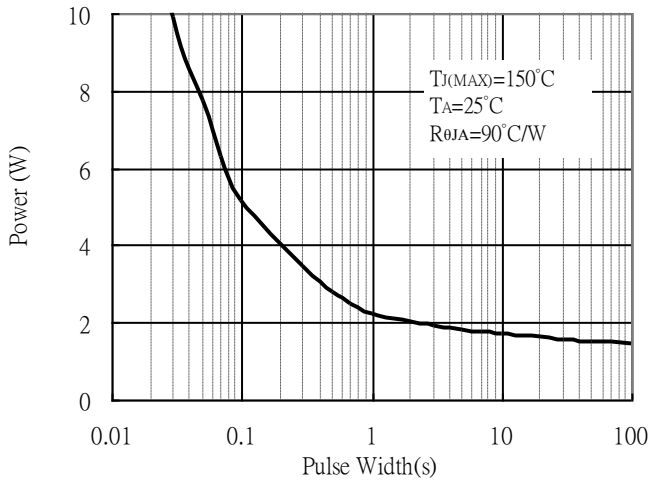
Capacitance vs Drain-to-Source Voltage



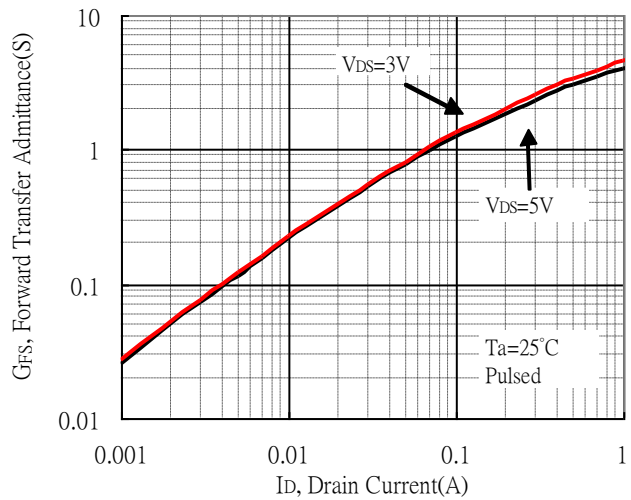
Threshold Voltage vs Junction Temperature



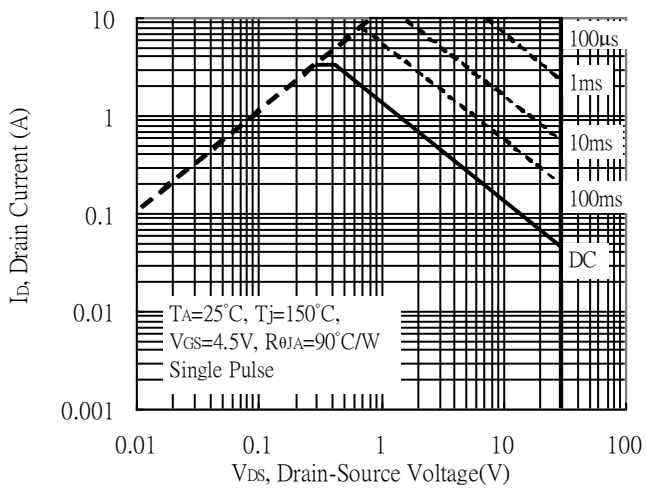
Single Pulse Power Rating, Junction to Ambient  
 (Note on page 2)



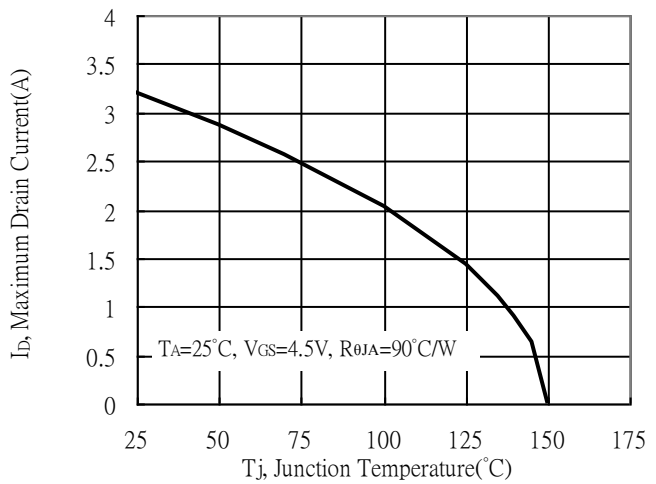
Forward Transfer Admittance vs Drain Current



Maximum Safe Operating Area

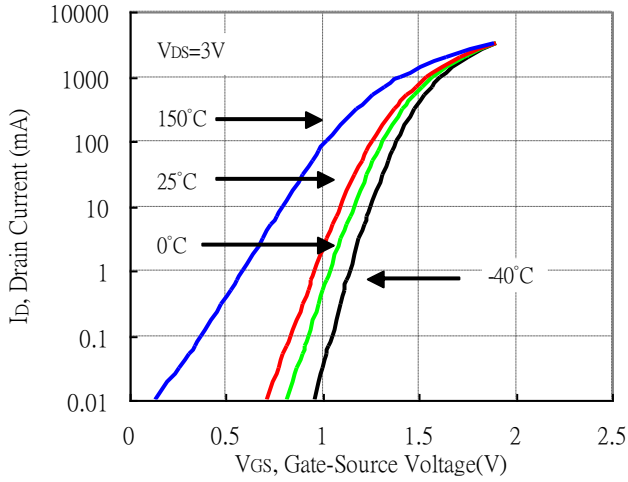


Maximum Drain Current vs Junction Temperature

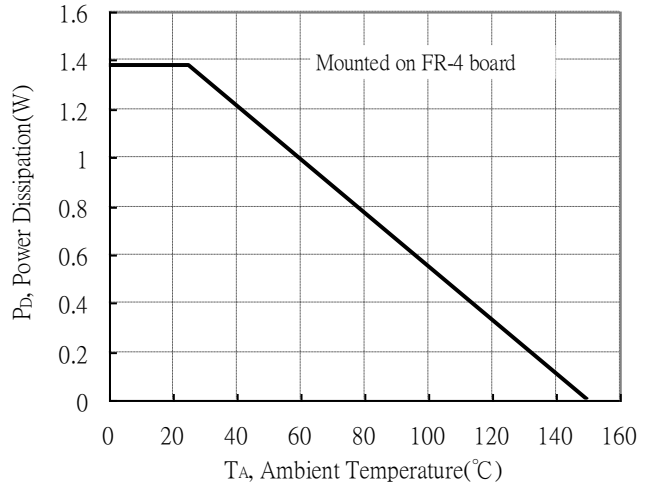


**Typical Characteristics(Cont.)**

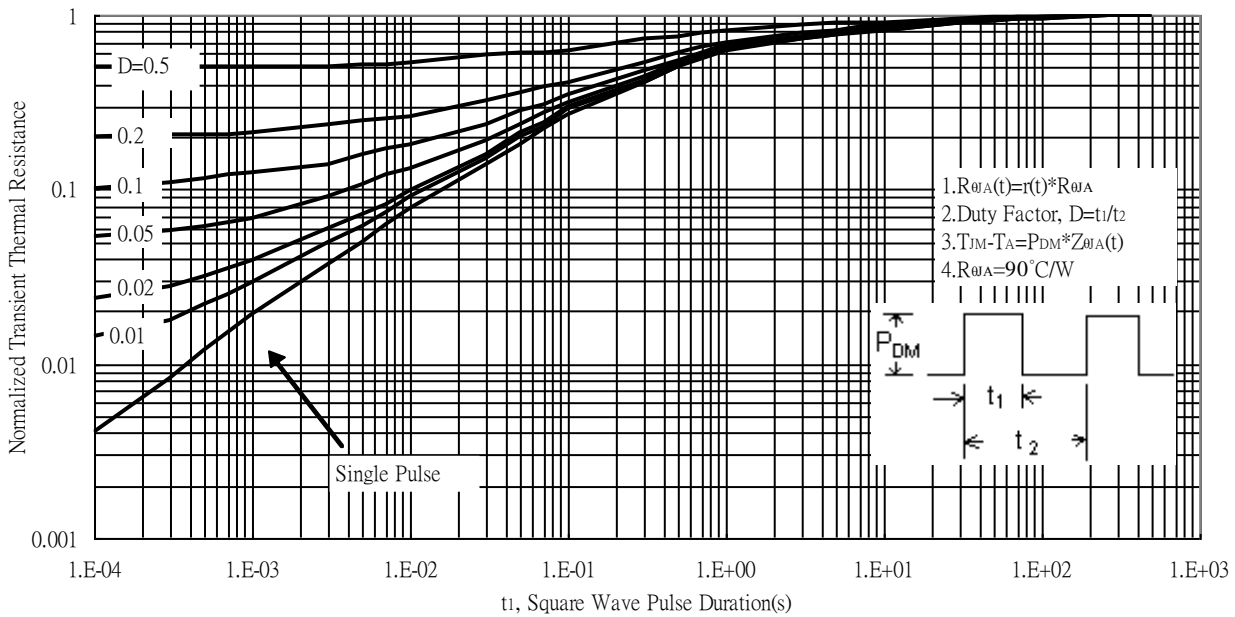
Typical Transfer Characteristics



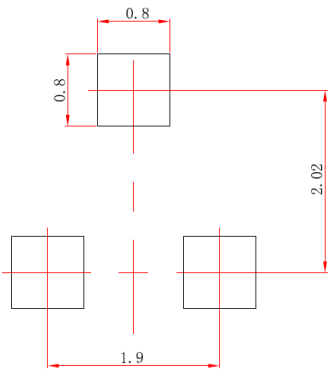
Power Derating Curve



Transient Thermal Response Curves

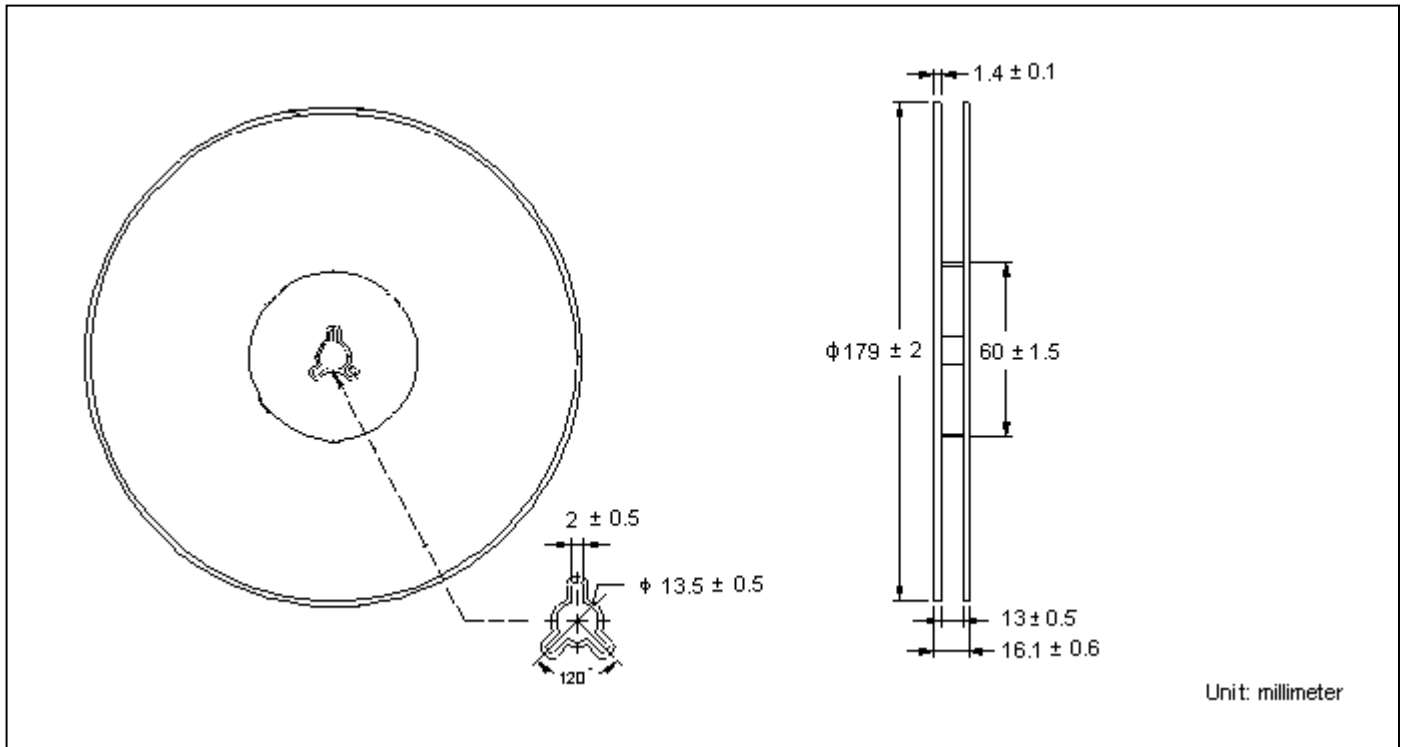


**Recommended Soldering Footprint**

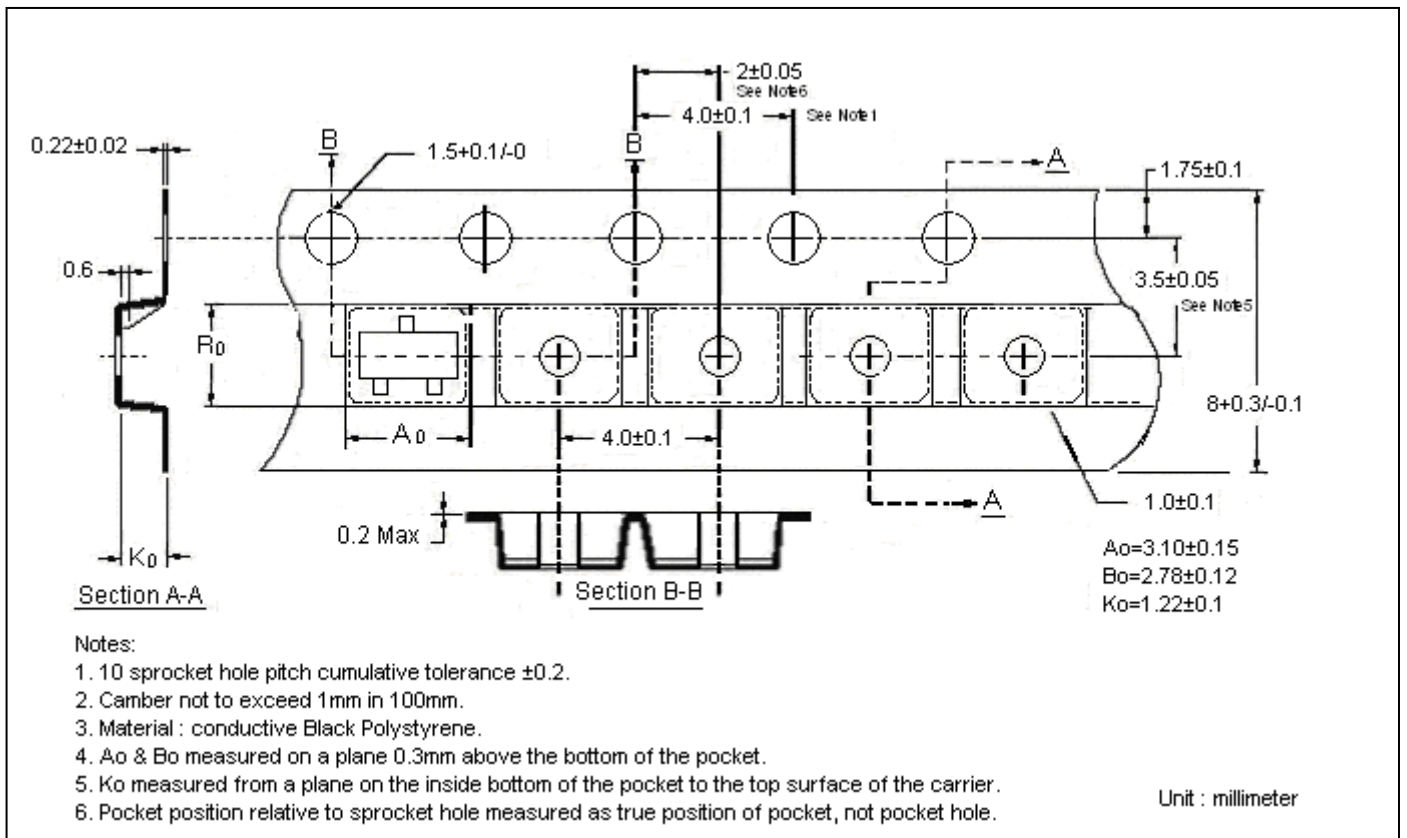


Unit : mm

**Reel Dimension**



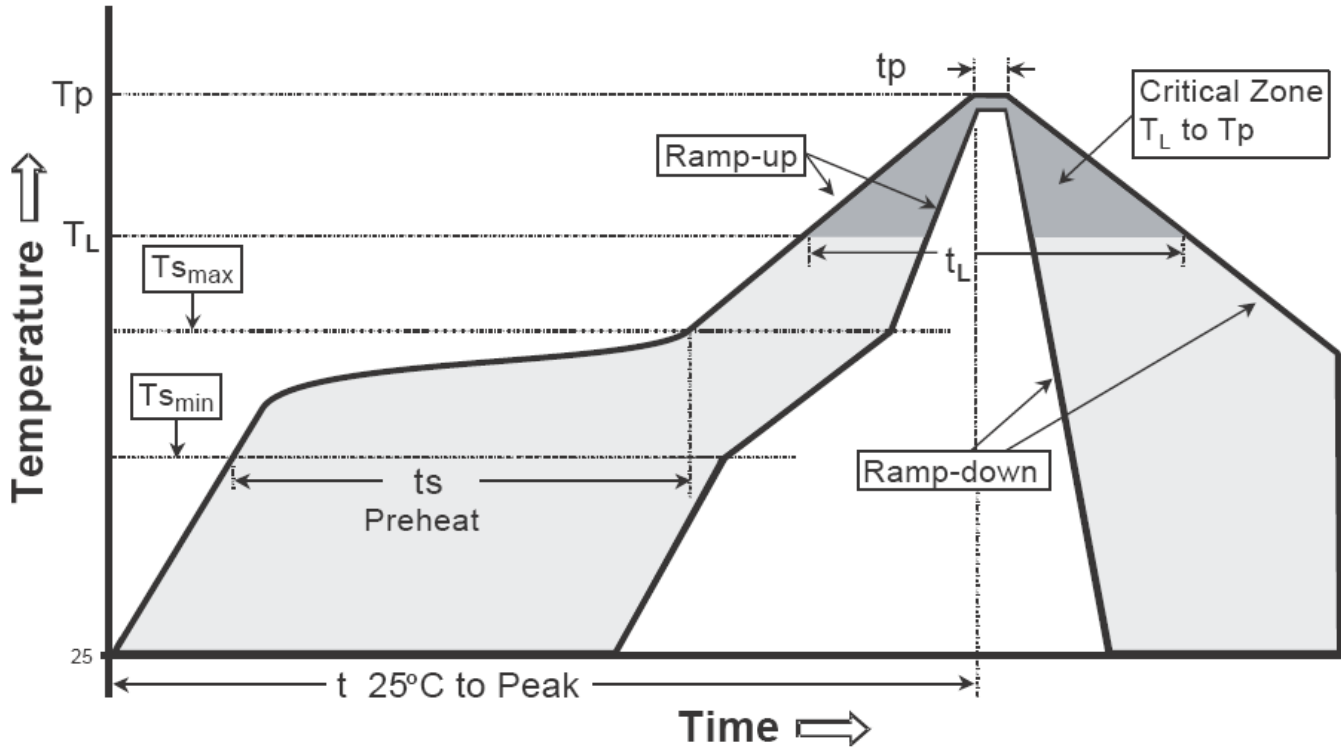
**Carrier Tape Dimension**



**Recommended wave soldering condition**

|                 |                  |                 |
|-----------------|------------------|-----------------|
| Product         | Peak Temperature | Soldering Time  |
| Pb-free devices | 260 +0/-5 °C     | 5 +1/-1 seconds |

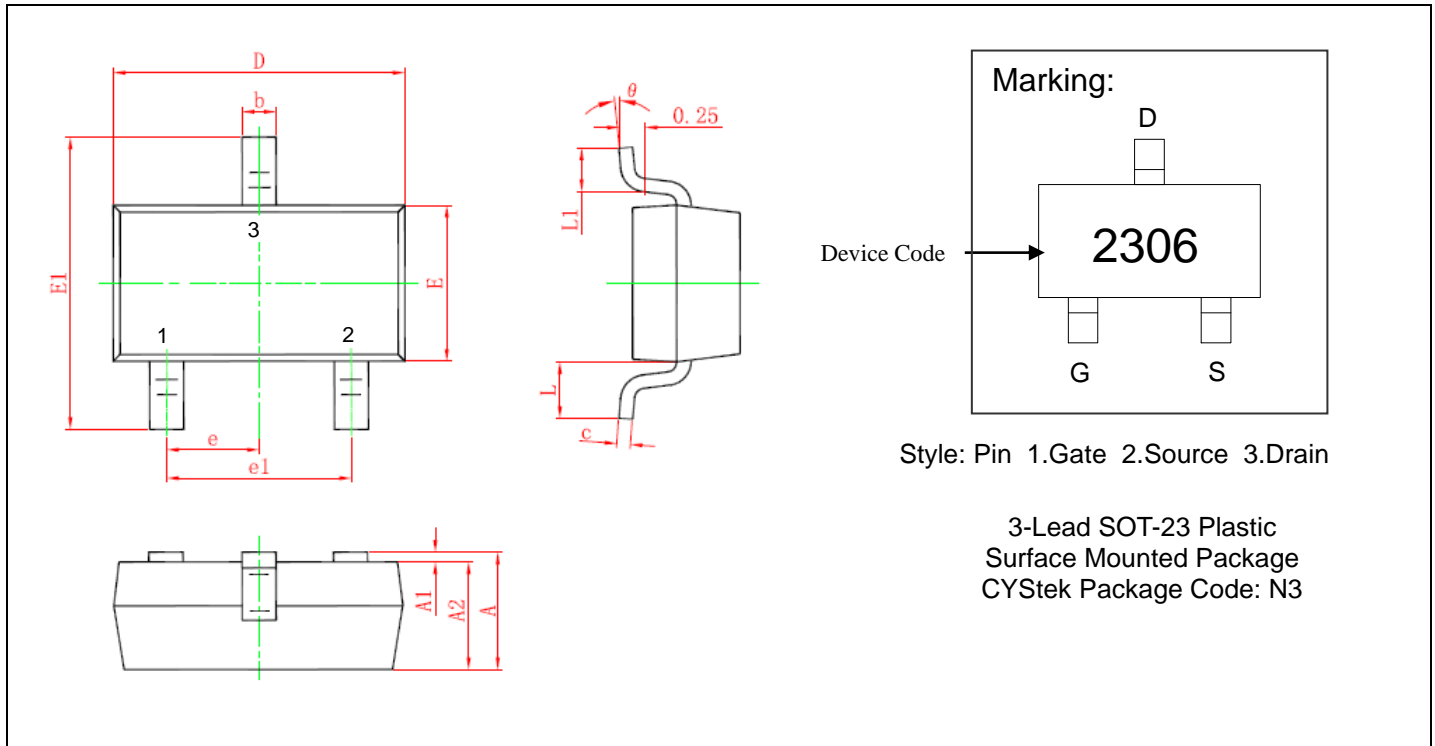
**Recommended temperature profile for IR reflow**



| Profile feature   | Sn-Pb eutectic Assembly | Pb-free Assembly |
|---|-------------------------|------------------|
| Average ramp-up rate (T <sub>smax</sub> to T <sub>p</sub> ) | 3°C/second max.         | 3°C/second max.  |
| Preheat   |                         |                  |
| -Temperature Min(T <sub>s min</sub> )                       | 100°C                   | 150°C            |
| -Temperature Max(T <sub>s max</sub> )                       | 150°C                   | 200°C            |
| -Time(t <sub>s min</sub> to t <sub>s max</sub> )            | 60-120 seconds          | 60-180 seconds   |
| Time maintained above:                                      |                         |                  |
| -Temperature (T <sub>L</sub> )                              | 183°C                   | 217°C            |
| - Time (t <sub>L</sub> )                                    | 60-150 seconds          | 60-150 seconds   |
| Peak Temperature(T <sub>P</sub> )                           | 240 +0/-5 °C            | 260 +0/-5 °C     |
| Time within 5°C of actual peak temperature(tp)              | 10-30 seconds           | 20-40 seconds    |
| Ramp down rate  | 6°C/second max.         | 6°C/second max.  |
| Time 25 °C to peak temperature                              | 6 minutes max.          | 8 minutes max.   |

Note : All temperatures refer to topside of the package, measured on the package body surface.

**SOT-23 Dimension**



| DIM | Inches |       | Millimeters |       | DIM | Inches     |       | Millimeters |       |
|-----|--------|-------|-------------|-------|-----|------------|-------|-------------|-------|
|     | Min.   | Max.  | Min.        | Max.  |     | Min.       | Max.  | Min.        | Max.  |
| A   | 0.035  | 0.045 | 0.900       | 1.150 | E1  | 0.089      | 0.100 | 2.250       | 2.550 |
| A1  | 0.000  | 0.004 | 0.000       | 0.100 | e   | 0.037 TYP. |       | 0.950 TYP.  |       |
| A2  | 0.035  | 0.041 | 0.900       | 1.050 | e1  | 0.071      | 0.079 | 1.800       | 2.000 |
| b   | 0.012  | 0.020 | 0.300       | 0.500 | L   | 0.022 REF. |       | 0.550 REF.  |       |
| c   | 0.003  | 0.006 | 0.080       | 0.150 | L1  | 0.012      | 0.020 | 0.300       | 0.500 |
| D   | 0.110  | 0.118 | 2.800       | 3.000 | θ   | 0°         | 8°    | 0°          | 8°    |
| E   | 0.047  | 0.055 | 1.200       | 1.400 |     |            |       |             |       |

Notes: 1.Controlling dimension: millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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